polycrystal silicon semiconductor or amorphous silicon semiconductor. A conventional photoelectric conversion device is designed as a best device so that semiconductor layers having a PN or PIN junction are laminated on a moncrystal silicon substrate or an insulating substrate and positive and negative electrodes are formed on the top and bottom surfaces of the semiconductor layers. Further, the junction surface of the PN or PIN junction has been conventionally designed substantially in parallel with the principal plane of the semiconductor layers or the substrate to irradiate a large amount of light onto the junction surface.--

On page 3, please replace the fourth full paragraph with the following substitute paragraph. Attached hereto is a marked-up copy of the amended substitute paragraph.

--Still further, the semiconductor film thus obtained has an electrical characteristic of 10 to 200cm^{-2}/Vsec in hole mobility, and 15 to 300^{-2}/Vsec in electron mobility. Therefore, the TFT has a remarkably high photoresponsivity.--

On page 9, please replace the seventh full paragraph with the following substitute paragraph. Attached hereto is a marked-up copy of the amended substitute paragraph.

--Through a series of processes as described above, the P-type TFT portion 100, the N-type TFT portion 200 and the photoelectric conversion device portion 300 are formed on the same glass substrate 1 using the same silicon semiconductor film. FIG 1(F) shows the image reading unit which is finally completed through the above processes. The following are characteristics (carrier mobility and threshold voltage Vth) of the P-type TFT and the N-type TFT, respectively.--